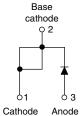
VS-MUR820PbF, VS-MUR820-N3

Vishay Semiconductors

Ultrafast Rectifier, 8 A FRED Pt®

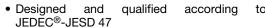




TO-220AC

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current



 Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>



DESCRIPTION / APPLICATIONS

VS-MUR820PbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

PRODUCT SUMMARY						
TO-220AC						
8 A						
200 V						
0.895 V						
See Recovery table						
175 °C						
Single die						

SYMBOL	TEST CONDITIONS	MAX.	UNITS
V_{RRM}		200	V
I _{F(AV)}	Total device, rated V _R , T _C = 150 °C	8	
I _{FSM}		100	Α
I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16	
T _J , T _{Stg}		-65 to +175	°C
	V _{RRM} I _{F(AV)} I _{FSM} I _{FM}	V_{RRM} $I_{F(AV)}$ I_{FSM} I_{FM} $Rated V_R, square wave, 20 kHz, T_C = 150 °C$	$\begin{array}{c cccc} V_{RRM} & 200 \\ \hline I_{F(AV)} & Total \ device, \ rated \ V_R, \ T_C = 150 \ ^{\circ}C \\ \hline I_{FSM} & 100 \\ \hline I_{FM} & Rated \ V_R, \ square \ wave, \ 20 \ kHz, \ T_C = 150 \ ^{\circ}C \\ \hline 16 & \\ \hline \end{array}$

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
Famous de la casa	V _F	I _F = 8 A	-	-	0.975	V	
Forward voltage		I _F = 8 A, T _J = 150 °C	-	-	0.895		
Payaraa laakaga aurrant		$V_R = V_R$ rated	-	-	5		
Reverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	250	μA	
Junction capacitance	C _T	V _R = 200 V	-	25	=	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	ı	8.0	ı	nΗ	



VS-MUR820PbF, VS-MUR820-N3

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt =$	$50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	-	35			
		I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25	no		
	t _{rr}	T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/μs	-	20	-	ns		
		T _J = 125 °C		-	34	-			
Dook roomen ourrent	I _{RRM}	T _J = 25 °C		-	1.7	-	Α		
Peak recovery current		IRRM	T _J = 125 °C	$V_{R} = 160 \text{ V}$	-	4.2	-	^	
Reverse recovery charge	Q _{rr}	Q _{rr}	T _J = 25 °C		-	23	-	nC	
			T _J = 125 °C		-	75	-	110	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	3.0			
Thermal resistance, junction to ambient	R _{thJA}		-	-	50	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-			
Waight			-	2.0	-	g		
Weight			-	0.07	-	OZ.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-220AC	MUR820					

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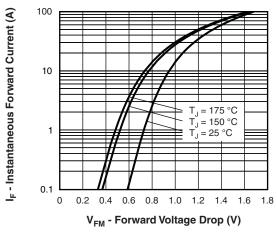


Fig. 1 - Maximum Forward Voltage Drop Characteristics

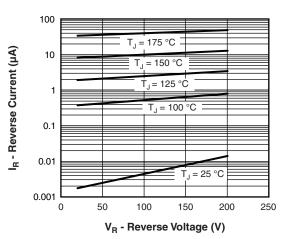


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

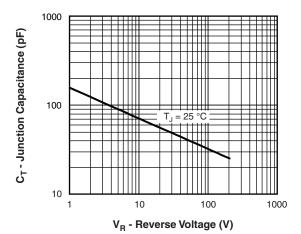


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

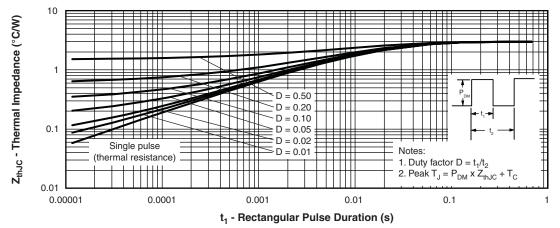


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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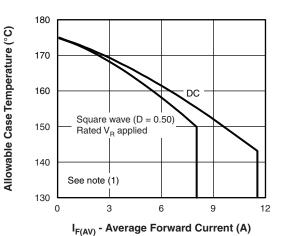


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

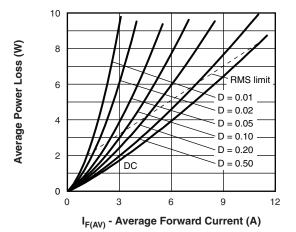
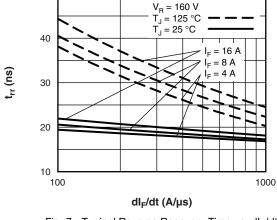


Fig. 6 - Forward Power Loss Characteristics



50

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

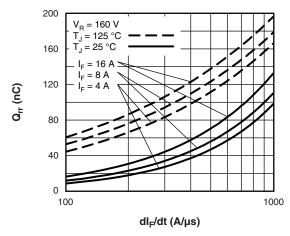


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$

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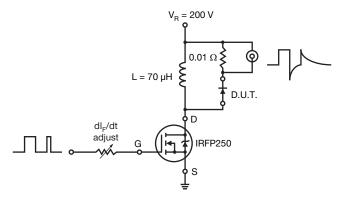
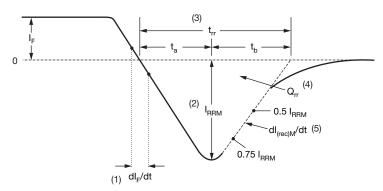


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

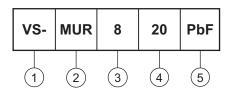
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-MUR820PbF, VS-MUR820-N3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

3 - Current rating (8 = 8 A)

Voltage rating (20 = 200 V)

5 - Environmental digit:

PbF = lead (Pb)-free and RoHS,compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-MUR820PbF	50	1000	Antistatic plastic tube				
VS-MUR820-N3	50	1000	Antistatic plastic tube				

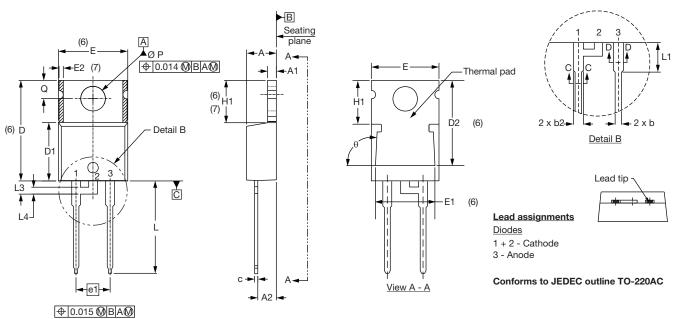
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95221</u>					
Deut verendinge information	TO-220ACPbF	www.vishay.com/doc?95224			
Part marking information	TO-220AC-N3	www.vishay.com/doc?95068			



Vishay Semiconductors

TO-220AC

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIM	IETERS	INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° to 93°		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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